	tegrated Device Technology, In 24 Silver Creek Valley Road In Jose, CA 96138			
		HANGE NOTICE (PCN)		
Product Affected: 74CBTLV3244Q	ATE: April 13, 2015 G, 74CBTLV3244QG8, GG, 74CBTLV3244PGG8	MEANS OF DISTINGUISHING CHANGED DEVICES: Product Mark Back Mark Date Code Prefix SA5 before datecode Other		
Contact: IDT PCN DESK		Attachment: Yes No		
E-mail: <u>pcndesk@idt.com</u>		Samples: Available upon request		
DESCRIPTION AND PURPOSE OF	CHANGE:			
 Die Technology Wafer Fabrication Process Assembly Process Equipment Material Testing Manufacturing Site Data Sheet Other 	This notification is to advise our customers that IDT has successfully completed the transfer of the above part numbers wafer fab production from IDT Hillsboro, Oregon (Fab 4) to Taiwan Semiconductor Manufacturing Corporation (TSMC). There is no expected change to the data sheet, package or backend manufacturing process. There is no change to ordering part number and device top mark.			
RELIABILITY/QUALIFICATION				
Based on wafer and component level qualification and characterization tests, there is no change to the performance or reliability of the product.				
to grant approval or request additional it will be assumed that this change is a	written notification of this chang information. If IDT does not re acceptable. ersion manufactured after the pr	ge. Please use the acknowledgement below or E-Mail ecceive acknowledgement within 30 days of this notice rocess change effective date until the inventory		
Customer:] Approval for shipments prior to effective date.		
Name/Date:	E-	Mail Address:		
Title:	Ph	none# /Fax# :		
CUSTOMER COMMENTS:				

IDT ACKNOWLEDGMENT OF RECEIPT:

RECD. BY:

DATE:



Integrated Device Technology, Inc. 6024 Silver Creek Valley Road San Jose, CA 96138

PRODUCT/PROCESS CHANGE NOTICE (PCN)

ATTACHMENT I - PCN # : W1503-02

PCN Type: Wafer Fab Manufacturing Site Change - IDT Fab 4 to TSMC

Data Sheet Change: No

Detail Of Change:

This notification is to advise our customers that IDT has successfully completed the transfer of the above part numbers wafer fab production from IDT Hillsboro, Oregon (Fab 4) to Taiwan Semiconductor Manufacturing Corporation (TSMC).

TSMC has closely matched the IDT Fab 4 process for this transferred part, using the same design rules of the existing product.

There is no expected change to the data sheet, package or backend manufacturing process. Characterization data of material manufactured at TSMC is comparable to material manufactured at IDT Fab 4, Hillsboro.

There is no change to ordering part number and device top mark.

Please contact your local IDT sales representative to request samples or additional information.



TSMC Transfer Qualification Test Result Summary

Technology Information: $0.5 \ \mu m, 3.3 \ V$

Fab Location: TSMC Fab 3

Technology Qualification Vehicle Test Summary – JESD47 Recommended Tests

Test / Conditions	Logic Vehicle: 40V024SA5
	Sample Size/ Rejects/ each lot
High Temperature Operating Life (Dynamic) JESD22-A108B, +125°C @ 1000 hours or equivalent	79 / 0
Temperature Cycle JESD22-A104B, -55°C -/125°C, 1000 cycles	45 / 0
High Temperature Storage Bake JESD22-A-103-B, 150°C, 1000 hrs	77 / 0
ESD: Human Body Model JESD22-A114F, Rating: 2000V	3 / 0
ESD: Charged Device Model JEDEC 22-101C, Rating: 500V	3 / 0
ESD: Machine Model JESD22-A115B, Rating: 200V	3 / 0
Latch-up JESD78B	6 / 0
Electrical Characterization per Datasheet conditions	10

Technology Qualification Vehicle Test Summary – Supplemental Tests

Test / Conditions	Logic Vehicle: 40V024SA5
	Sample Size/ Rejects/ each lot
Ball Shear Test JESD22-B116-A, Ball Shear Strength > 5.7g	5 / 0
Highly Accelerated Stress Test (HAST) EIA/JESD22-A110B, 130°C/85%R.H. Vcc max for 100 hours.	45 / 0
Autoclave EIA/JESD22-A102C, 168hrs @ 2 ATM, Saturated Steam @ 121°C	45 / 0

Note: For HAST, Autoclave and Temperature Cycle, samples have been subjected to pre-conditioning per JESD22-A113